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NTE5360 Silicon Controlled Rectifier (SCR) for High Speed Switching, 600V, 35 Amp, TO48

Absolute Maximum Ratings and Electrical Characteristics:

Repetitive Peak Off State Voltage (Gate Open, $T_J = +110^{\circ}\text{C}$), V_{DRM}	600V
Repetitive Peak Reverse Voltage (Gate Open, $T_J = +110^{\circ}\text{C}$), V_{RRM}	600V
RMS On-State Current ($T_C = +80^{\circ}\text{C}$, 360° Conduction Angle), $I_{T(RMS)}$	40A
Peak Surge (Non-Repetitive) On-State Current (One Cycle, 50 or 60Hz), I_{TSM}	400A
Peak Gate Trigger Current ($3\mu\text{s}$ Max), I_{GTM}	2A
Peak Gate Power ($I_{GT} \leq I_{GTM}$), P_{GM}	20W
Average Gate Power Dissipation, $P_{G(AV)}$	500mW
Maximum Repetitive Peak Off-State Current (At V_{DRM} , $T_C = +110^{\circ}\text{C}$), I_{DRM}	1.0mA
Maximum Repetitive Peak Reverse Current (At V_{RRM} , $T_C = +110^{\circ}\text{C}$), I_{RRM}	1.0mA
Maximum Peak On-State Voltage ($T_C = +25^{\circ}\text{C}$, $I_T = 40\text{A}$), V_{TM}	1.6V
Maximum DC Holding Current (Gate Open, $T_C = +25^{\circ}\text{C}$), I_H	50mA
Critical Rate of Rise of Off-State Voltage (Gate Open, $T_C = +110^{\circ}\text{C}$), dv/dt	200V/ μs
Maximum DC Gate Trigger Current ($V_A = 12\text{V}$, $R_L = 60\Omega$, $T_C = +25^{\circ}\text{C}$), I_{GT}	25mA
Maximum DC Gate Trigger Voltage ($V_A = 12\text{V}$, $R_L = 60\Omega$, $T_C = +25^{\circ}\text{C}$), V_{GT}	2.0V
gate Controlled Turn-On Time (For t_d and t_r , $I_{GT} = 150\text{mA}$, $T_C = +25^{\circ}\text{C}$), t_{gt}	2.5 μs
Operating Temperature Range, T_{opr}	-40° to $+150^{\circ}\text{C}$
Storage Temperature Range, T_{stg}	-40° to $+150^{\circ}\text{C}$
Typical Thermal Resistance, Junction-to-Case, R_{thJC}	1.4 $^{\circ}\text{C}/\text{W}$

